

ABSTRACT OF THE DISCLOSURE

A method or process of manufacturing on-chip bypass capacitors on a VLSI device (or chip) is improved by utilizing a high-dielectric constant metal-insulator-metal (MIM) capacitor manufacturing process. The high-k constant MIM capacitor may include a lower electrode in a first metal layer of a VLSI device, a substantially thin layer of high-k insulator (e.g., silicon nitride at an interface of the first metal layer and a via, and an upper electrode form in a second metal layer. The via provides a channel between the second metal layer to the high-k insulator.

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